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Docket No. YOR920020105PCT

AMENDMENTS TO THE CLAIMS:

Please cancel claims 7-18 without prejudice or disclaimer.

- 1. (Currently amended) A circuit comprising:
 - a template comprising first and second layers;
- a semiconductor material <u>self-assembled</u> self-assembled on a <u>side of</u> said <u>first layer of</u> said template; and
- a <u>self-assembled</u> connection between the semiconductor material and the <u>second layer of said</u> template to form-said-eireuit.
- 2. (Currently amended) The circuit of claim 1, wherein said circuit comprises:
 - a first metal layer on a substrate;
 - an insulating layer on said first metal layer;
 - a second metal layer on said insulating layer;
- a self-assembled first semi-conductivity type material on one side of said first metal layer;
- a self-assembled second semi-conductivity type material on the other side of said first metal layer; and
- a self-assembled nanowire extending between a field concentrator on said <u>second first</u>
 metal layer and <u>at least</u> one of said first semi-conductivity type material and said second
 semi-conductivity type material to form said self-assembled connection.
- (Original) The circuit of claim 2, wherein said first semi-conductivity type material comprises a p-type material.
- (Original) The circuit of claim 2, wherein said second semi-conductivity type material comprises an n-type material.
- 5. (Original) The circuit of claim 2, wherein said self-assembled first semi-conductivity type

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material comprises organic molecules on one edge of said gold layer.

 (Original) The circuit of claim 2, wherein said self-assembled second semi-conductivity type material comprises organic molecules on one edge of said gold layer,

7-18. (Canceled)

19. (New) A circuit comprising:

a first metal layer formed on a substrate;

an insulating layer formed on said first metal layer;

a second metal layer formed on said insulating layer;

a first self-assembled organic semiconductor material formed on a first side of said first metal layer:

a second self-assembled organic semiconductor material on a second side of said first metal layer; and

a self-assembled nanowire formed between said first metal layer and at least one of said first and second self-assembled organic semiconductor materials.

- 20. (New) The circuit of claim 19, wherein said first and second self-assembled organic semiconductor materials comprise different conductivity types.
- 21. (New) The circuit of claim 19, wherein said first metal layer comprises one of gold, silver and platinum.
- 22. (New) The circuit of claim 19, wherein said second metal layer comprises an aluminum layer.
- 23. (New) The circuit of claim 19, wherein an end of said first and second self-assembled organic semiconductor materials comprises a first termination which bonds to a surface of

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said first metal layer.

24. (New) The circuit of claim 19, wherein said first termination comprises a sulfur atom.

25. (New) The circuit of claim 19, wherein said second metal layer comprises a field

concentrator, said self-assembled nanowire being formed on said field concentrator.

26. (New) The circuit of claim 19, wherein another end of said first and second self-

assembled organic semiconductor materials comprises a second termination, said self-

assembled nanowire being bonded to said second termination.

27. (New) The circuit of claim 19, wherein said second termination comprises a sulfur atom.

28. (New) The circuit of claim 19, wherein said nanowire comprises a gold nanowire.

29. (New) A self-assembled structure for electrically connecting layers in a circuit including a

first metal layer formed on a substrate, an insulating layer formed on the first metal layer, and

a first self-assembled organic semiconductor material formed on a first side of said

a second metal layer formed on the insulating layer, said structure comprising:

first metal laver:

a second self-assembled organic semiconductor material on a second side of said first

metal layer; and

a self-assembled nanowire formed between said first metal layer and at least one of

said first and second self-assembled organic semiconductor materials.

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